

V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (mΩ)	I <sub>D</sub> (A)
30	36 @ V <sub>GS</sub> = 10V	5.9
	53 @ V <sub>GS</sub> = 4.5V	4.9

### **Features**

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

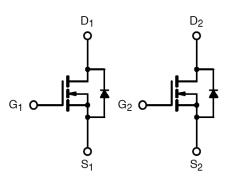
### **Application**

- High-Side DC/DC Conversion
- Notebook
- Sever

### **Ordering Information**

Part No.	Package	Packing		
TSM4936DCS RL	SOP-8	2.5Kpcs / 13" Reel		

### **Block Diagram**



**Dual N-Channel MOSFET** 

#### **Absolute Maximum Rating** (Ta = 25°C unless otherwise noted)

Parameter		Limit	Unit		
	V <sub>DS</sub>	30	V		
	V <sub>GS</sub>	±20	V		
	Ι <sub>D</sub>	5.9	А		
Pulsed Drain Current		40	А		
Continuous Source Current (Diode Conduction) <sup>a,b</sup>		1.0	А		
Ta = 25°C	- P <sub>D</sub>	3.0	W		
Ta = 75°C		2.1	VV		
Operating Junction Temperature		+150	°C		
Operating Junction and Storage Temperature Range		- 55 to +150	°C		
	Ta = 25°C Ta = 75°C		$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$		

#### **Thermal Performance**

Symbol	Limit	Unit
Rθ <sub>JF</sub>	32	°C/W
Rθ <sub>JA</sub>	50	°C/W
	Rθ <sub>JF</sub>	R $\Theta_{JF}$ 32

Notes:

a. Pulse width limited by the Maximum junction temperature

b. Surface Mounted on FR4 Board, t  $\leq$  10 sec.



#### Ph COMP ANCE

# **TSM4936D 30V N-Channel MOSFET**

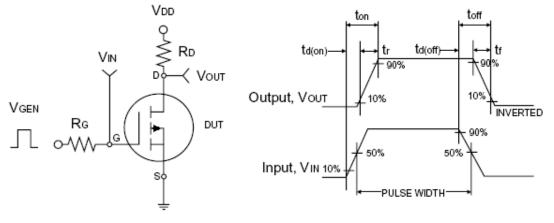
### **Electrical Specifications**

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_{D} = 250uA$	BV <sub>DSS</sub>	30			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	V <sub>GS(TH)</sub>	1	1.4	3	V
Gate Body Leakage	$V_{GS}$ = ±20V, $V_{DS}$ = 0V	I <sub>GSS</sub>			±100	nA
Zero Gate Voltage Drain Current	$V_{DS}$ = 24V, $V_{GS}$ = 0V	I <sub>DSS</sub>			1.0	μA
On-State Drain Current <sup>a</sup>	V <sub>DS</sub> ≥ 5V, V <sub>GS</sub> = 10V	I <sub>D(ON)</sub>	30			А
Drain Course On State Desistence <sup>a</sup>	in-Source On-State Resistance <sup>a</sup> $\frac{V_{GS} = 10V, I_D = 5.9A}{V_{GS} = 4.5V, I_D = 4.9A} R_{DS(ON)}$		32	36	mΩ	
Drain-Source On-State Resistance			42	53		
Forward Transconductance <sup>a</sup>	V <sub>DS</sub> = 15V, I <sub>D</sub> = 5.9A	g <sub>fs</sub>		15		S
Diode Forward Voltage	I <sub>S</sub> = 1A, V <sub>GS</sub> = 0V	V <sub>SD</sub>		0.76	1.0	V
Dynamic <sup>ь</sup>						
Total Gate Charge		Qg	-	13		
Gate-Source Charge	V <sub>DS</sub> = 15V, I <sub>D</sub> = 5.9A, V <sub>GS</sub> = 10V	Q <sub>gs</sub>		4.2		nC
Gate-Drain Charge		Q <sub>gd</sub>		3.1		
Input Capacitance	$V_{DS} = 15V, V_{GS} = 0V,$	C <sub>iss</sub>		610		
Output Capacitance		C <sub>oss</sub>		100		pF
Reverse Transfer Capacitance	f = 1.0MHz	C <sub>rss</sub>		77		
Switching <sup>c</sup>	•	·				
Turn-On Delay Time	- V <sub>DD</sub> = 15V, R <sub>L</sub> = 15Ω, I <sub>D</sub> = 1A, V <sub>GEN</sub> = 10V,	t <sub>d(on)</sub>		9.1		
Turn-On Rise Time		t <sub>r</sub>		16.5		
Turn-Off Delay Time		t <sub>d(off)</sub>		23		nS
Turn-Off Fall Time	$R_{G} = 6\Omega$	t <sub>f</sub>		3.5		

Notes:

a. pulse test: PW  $\leq$ 300µS, duty cycle  $\leq$ 2% b. For DESIGN AID ONLY, not subject to production testing.

b. Switching time is essentially independent of operating temperature.



Switching Test Circuit

Switchin Waveforms



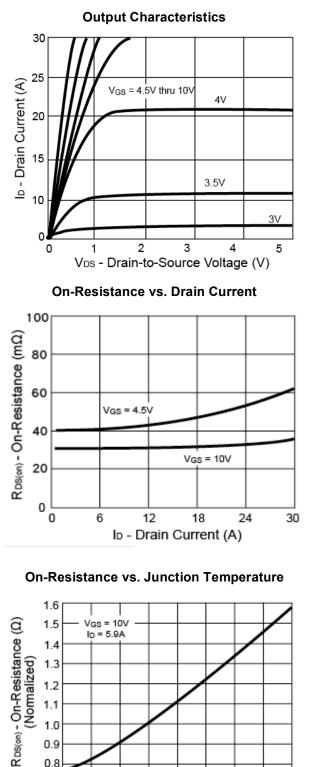
1.1 1.0

0.9 0.8 0.6

> -50 -25

## **TSM4936D 30V N-Channel MOSFET**

#### Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)



25

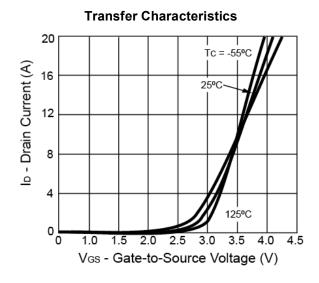
50

Tj - Junction Temperature (°C)

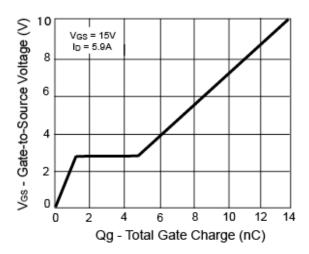
75

100

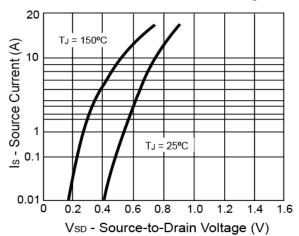
0



**Gate Charge** 



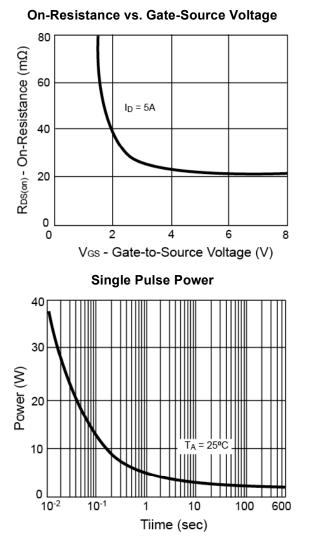
Source-Drain Diode Forward Voltage

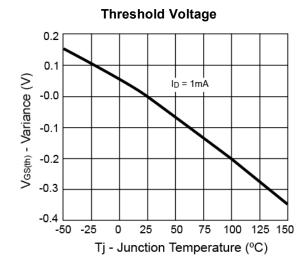


125 150

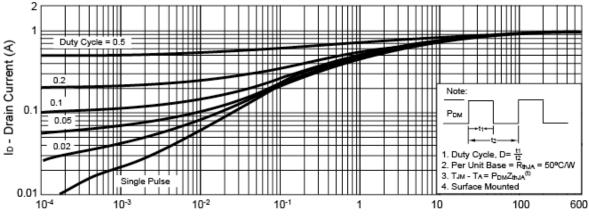


### Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)





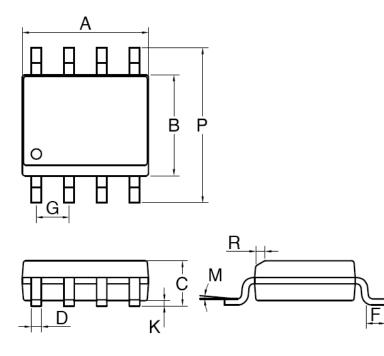
#### Normalized Thermal Transient Impedance, Junction-to-Ambient



Square Wave Pulse Duration (sec)

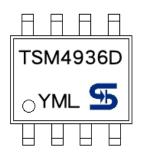


### **SOP-8 Mechanical Drawing**



SOP-8 DIMENSION					
DIM	MILLIMETERS		INCHES		
	MIN	MAX	MIN	MAX.	
Α	4.80	5.00	0.189	0.196	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.05BSC		
K	0.10	0.25	0.004	0.009	
М	0°	7°	0°	7°	
Р	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	

### **Marking Diagram**



- Y = Year Code
- M = Month Code

(A=Jan, B=Feb, C=Mar, D=Apl, E=May, F=Jun, G=Jul, H=Aug, I=Sep, J=Oct, K=Nov, L=Dec)

L = Lot Code



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